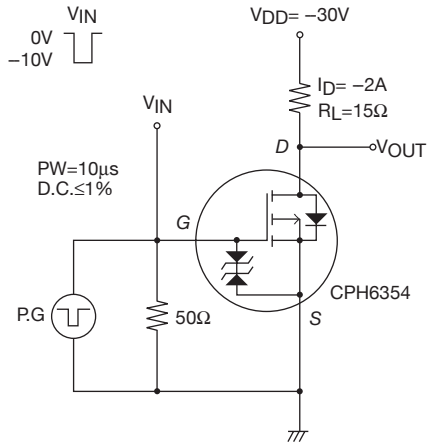
Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Value			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=−1mA, V_{GS}=0V	−60			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=−60V, V_{GS}=0V			−1	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±16V, V_{DS}=0V			±10	μA
Gate Threshold Voltage	V_{GS}(th)	V_{DS}=−10V, I_D=−1mA	−1.2		−2.6	V
Forward Transconductance	g_{FS}	V_{DS}=−10V, I_D=−2A		4.8		S
Static Drain-to-Source On-State Resistance	R_{DS}(on)1	I_D=−2A, V_{GS}=−10V		77	100	mΩ
	R_{DS}(on)2	I_D=−1A, V_{GS}=−4.5V		96	135	mΩ
	R_{DS}(on)3	I_D=−1A, V_{GS}=−4V		103	145	mΩ
Input Capacitance	Ciss	V_{DS}=−20V, f=1MHz		600		pF
Output Capacitance	Coss			60		pF
Reverse Transfer Capacitance	Crss			50		pF
Turn-ON Delay Time	t_d(on)	See specified Test Circuit.		5.8		ns
Rise Time	t_r			12		ns
Turn-OFF Delay Time	t_d(off)			78		ns
Fall Time	t_f			40		ns
Total Gate Charge	Qg	V_{DS}=−30V, V_{GS}=−10V, I_D=−4A		14		nC
Gate-to-Source Charge	Qgs			1.6		nC
Gate-to-Drain “Miller” Charge	Qgd			3.4		nC
Forward Diode Voltage	V_{SD}	I_S=−4A, V_{GS}=0V		−0.84	−1.2	V

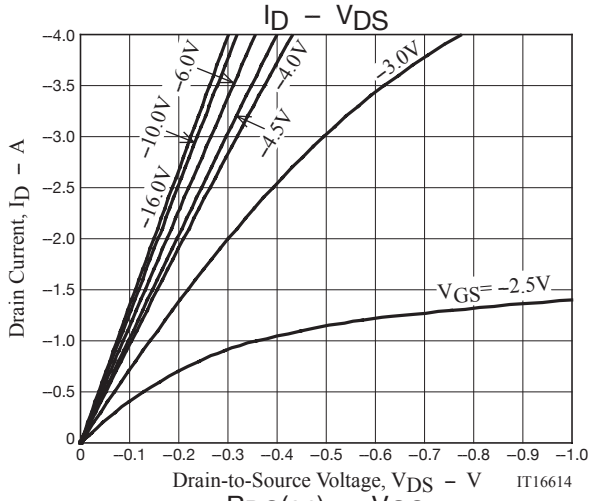
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

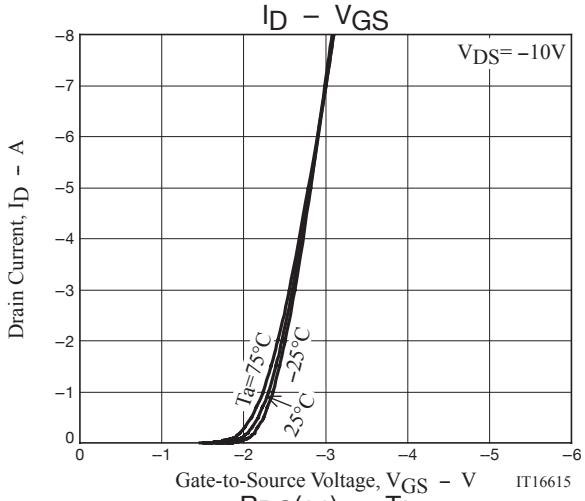
Switching Time Test Circuit

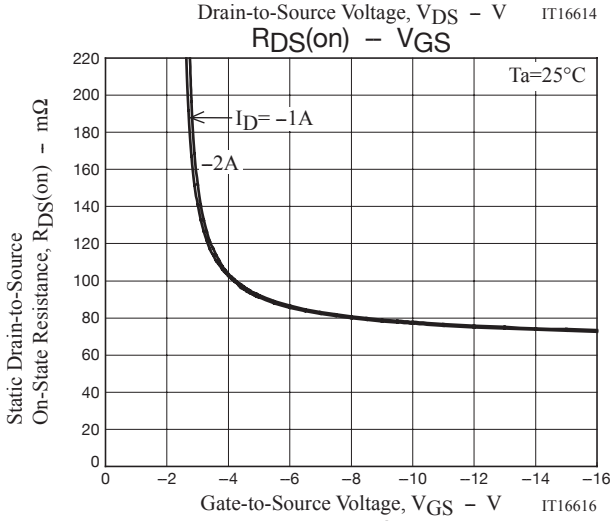


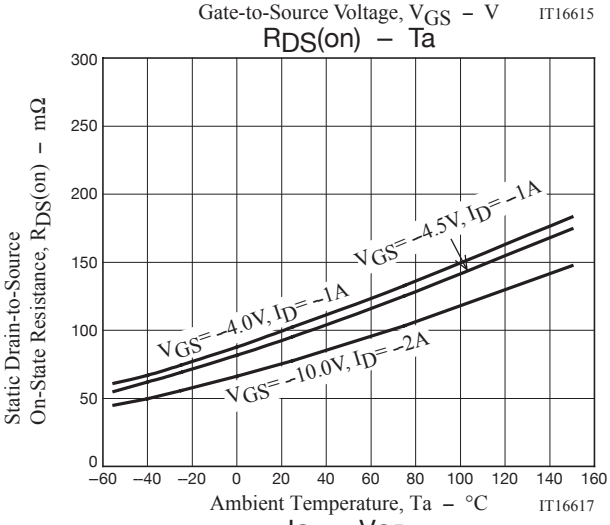
ORDERING INFORMATION

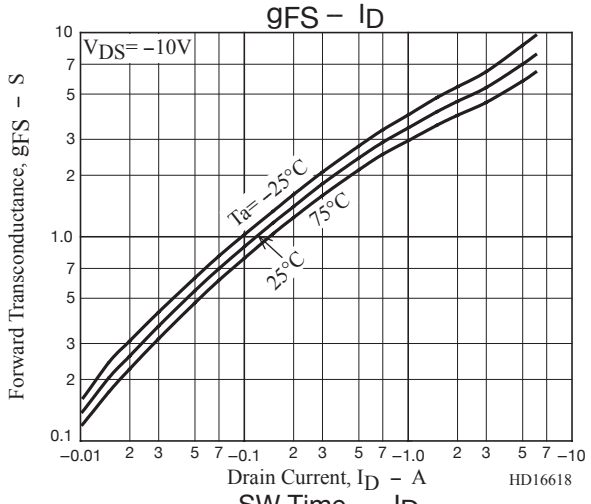
Device	Package	Shipping	memo
CPH6354-TL-H	CPH6	3,000pcs./reel	Pb-Free and Halogen Free
CPH6354-TL-W			

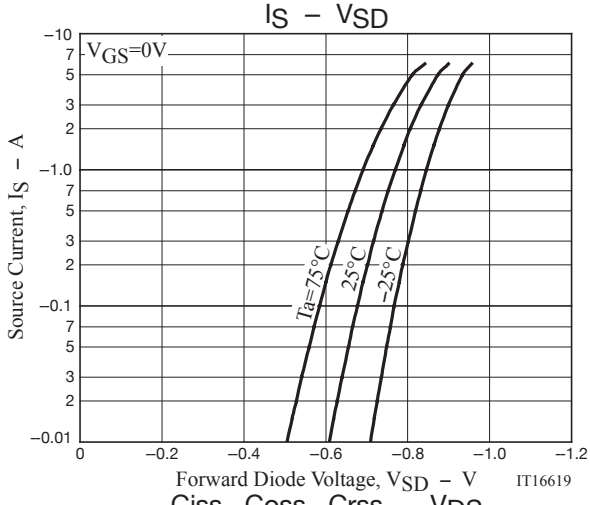


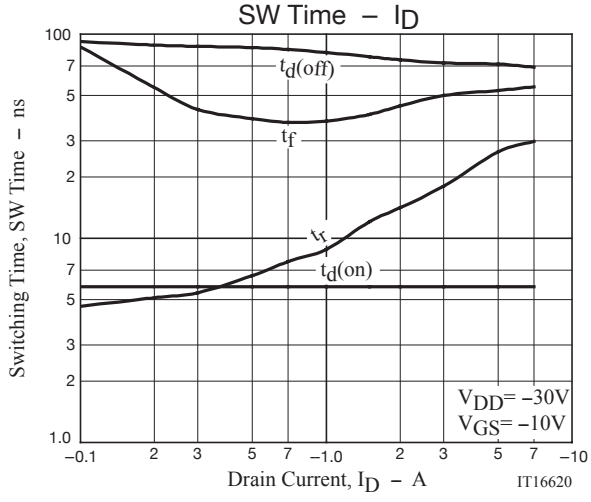


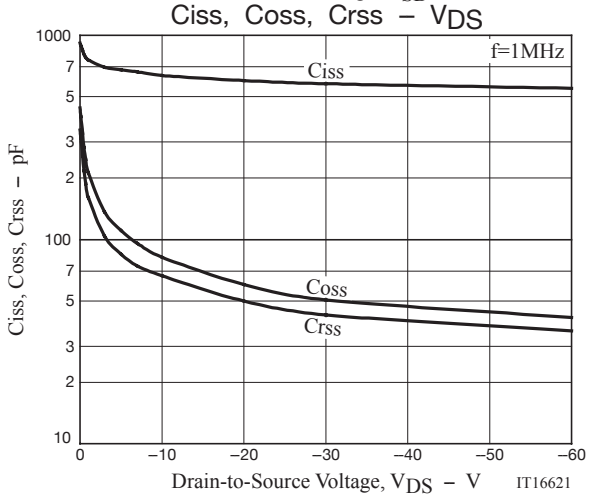


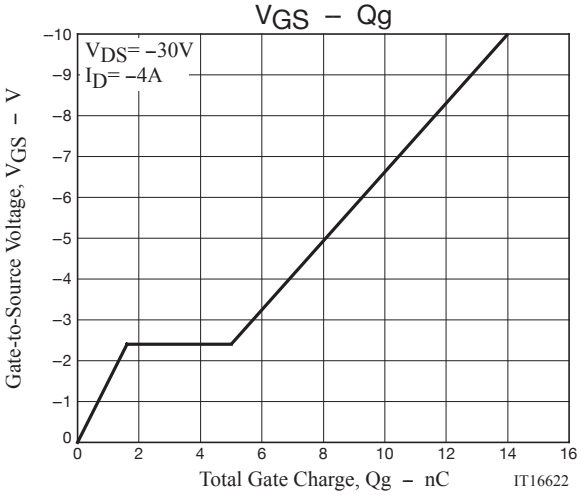


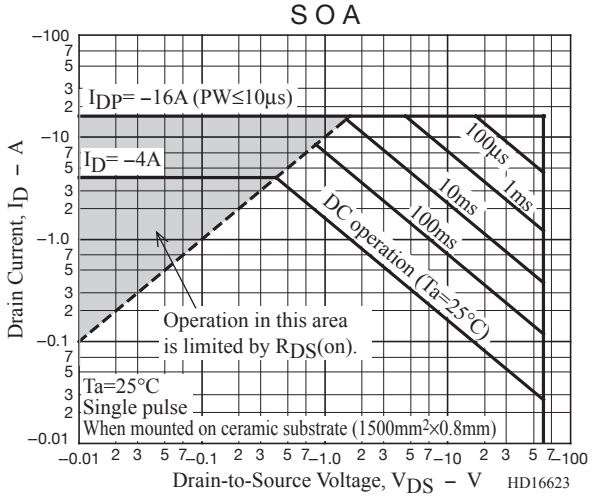


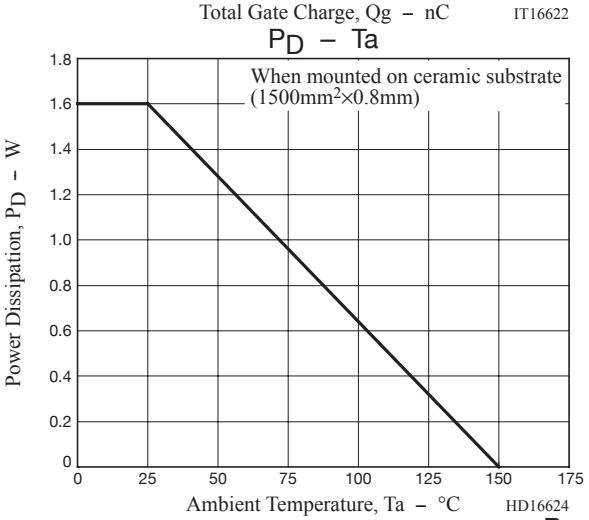


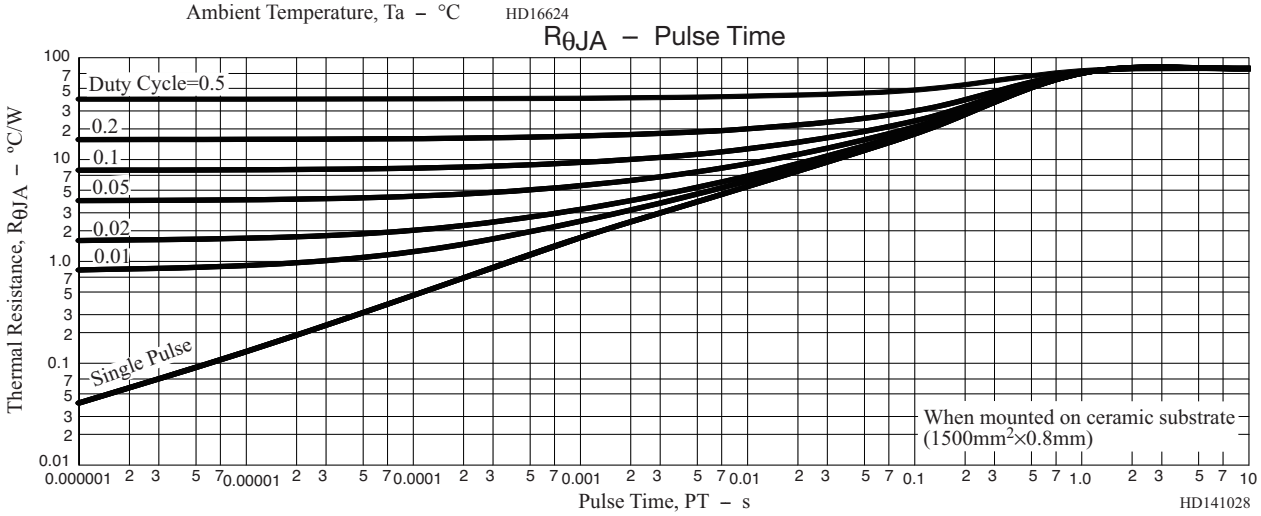






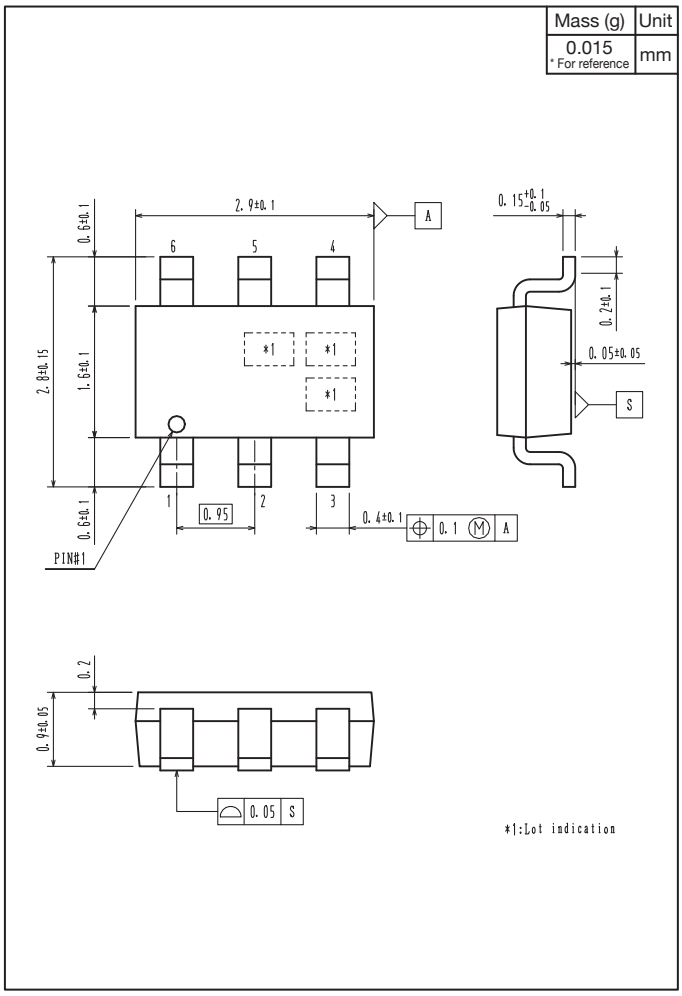




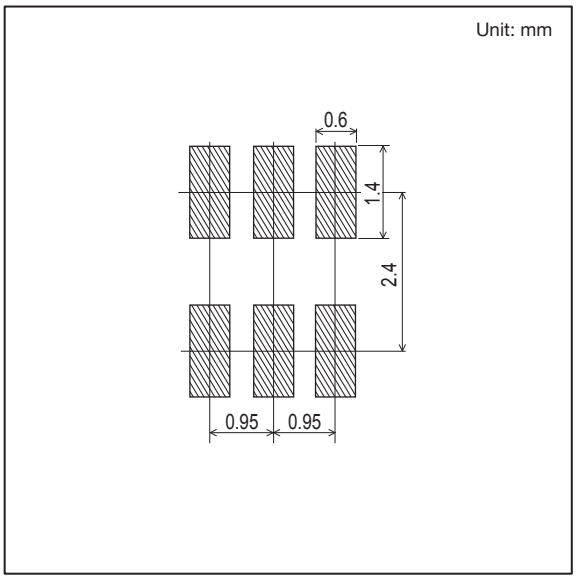


Outline Drawing

CPH6354-TL-H, CPH6354-TL-W



Land Pattern Example



Note on usage : Since the CPH6354 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.